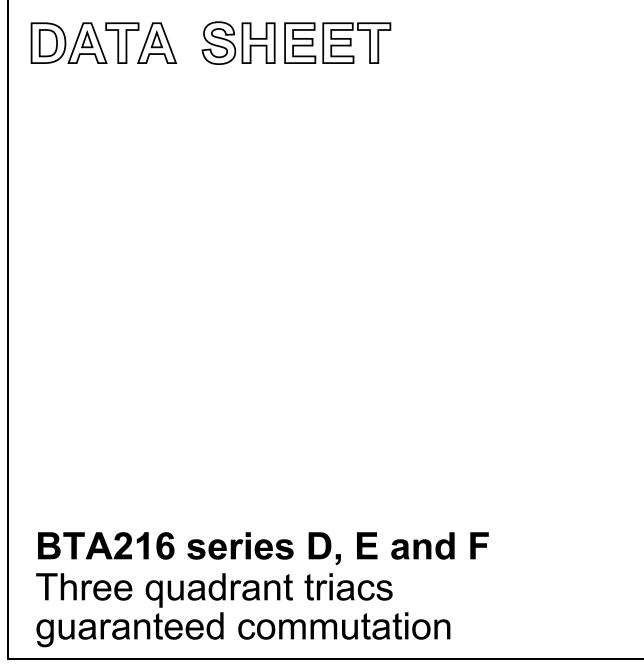
DISCRETE SEMICONDUCTORS



Product specification

April 2002



MAX.

600D

600E

600F

600

16

140

UNIT

٧

A

А

## Three quadrant triacs guaranteed commutation

## BTA216 series D, E and F

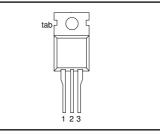
## **GENERAL DESCRIPTION**

Passivated guaranteed commutation triacs in a plastic envelope intended for use in motor control circuits or with other highly inductive These devices balance loads. the requirements of commutation performance and gate sensitivity. The "sensitive gate" E series and "logic level" D series are intended for interfacing with low power drivers, including micro controllers.

### **PINNING - TO220AB**

### PIN DESCRIPTION

#### 1 main terminal 1 2 main terminal 2 3 gate main terminal 2 tab



QUICK REFERENCE DATA

current

PARAMETER

Repetitive peak off-state

Non-repetitive peak on-state

voltages RMS on-state current

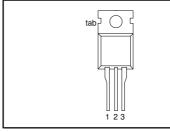


BTA216-

**BTA216-**

**BTA216-**

SYMBOL



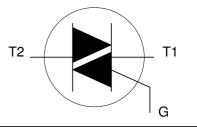
**PIN CONFIGURATION** 

SYMBOL

V<sub>DRM</sub>

T(RMS)

I<sub>TSM</sub>



## LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

| SYMBOL  | PARAMETER   | CONDITIONS   | MIN.        | MAX.             | UNIT        |
|---|---|--|-------------|------------------|-------------|
| V <sub>DRM</sub>  | Repetitive peak off-state voltages  |  | -           | 600 <sup>1</sup> | V           |
| I <sub>T(RMS)</sub>   | RMS on-state current  | full sine wave;<br>T <sub>mb</sub> ≤ 99 °C                                     | -           | 16               | А           |
|   | Non-repetitive peak<br>on-state current   | full sine wave;<br>$T_j = 25$ °C prior to<br>surge<br>t = 20 ms<br>t = 16.7 ms | -<br>-      | 140<br>150       | A           |
| l <sup>2</sup> t<br>dI <sub>T</sub> /dt                     | I <sup>2</sup> t for fusing<br>Repetitive rate of rise of<br>on-state current after<br>triggering |  | -           | 98<br>100        | A²s<br>A/μs |
| $\begin{matrix} I_{GM} \\ P_{GM} \\ P_{G(AV)} \end{matrix}$ | Peak gate current<br>Peak gate power<br>Average gate power  | over any 20 ms   | -<br>-<br>- | 2<br>5<br>0.5    | A<br>W<br>W |
| T <sub>stg</sub><br>T <sub>j</sub>                          | Storage temperature<br>Operating junction<br>temperature  | period   | -40<br>-    | 150<br>125       | °C<br>°C    |

<sup>1</sup> Although not recommended, off-state voltages up to 800V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 15 A/µs.

# Three quadrant triacs guaranteed commutation

## BTA216 series D, E and F

## THERMAL RESISTANCES

| SYMBOL                                      | PARAMETER  | CONDITIONS                              | MIN. | TYP.         | MAX.            | UNIT              |
|---|--|---|------|--------------|-----------------|-------------------|
| R <sub>th j-mb</sub><br>R <sub>th j-a</sub> | Thermal resistance<br>junction to mounting base<br>Thermal resistance<br>junction to ambient | full cycle<br>half cycle<br>in free air | -    | -<br>-<br>60 | 1.2<br>1.7<br>- | K/W<br>K/W<br>K/W |

## STATIC CHARACTERISTICS

 $T_j = 25$  °C unless otherwise stated

| SYMBOL                            | PARAMETER                         | CONDITIONS  | MIN.    | MAX.        |     | UNIT     |          |
|-----------------------------------|-----------------------------------|---|---------|-------------|-----|----------|----------|
|                                   |                                   | BTA216-   |         | D           | E   | F        |          |
| I <sub>GT</sub>                   | Gate trigger current <sup>2</sup> | $V_{\rm D} = 12 \text{ V}; I_{\rm T} = 0.1 \text{ A}$   |         |             |     |          |          |
|                                   |                                   | T2+ G+  | -       | 5<br>5<br>5 | 10  | 25       | mA       |
|                                   |                                   | T2+ G-  | -       | 5           | 10  | 25       | mA       |
| Ι.                                |                                   | T2- G-  | -       | 5           | 10  | 25       | mA       |
| I IL                              | Latching current                  | $V_{\rm D} = 12 \text{ V}; I_{\rm GT} = 0.1 \text{ A}$  |         | 4.5         | 05  | 00       |          |
|                                   |                                   | T2+G+   | -       | 15          | 25  | 30       | mA       |
|                                   |                                   | T2+ G-<br>  T2- G-                                      | -       | 25<br>25    | 30  | 40<br>40 | mA<br>mA |
|                                   |                                   | 12- G-  | -       | 25          | 30  | 40       | mA       |
| I <sub>H</sub>                    | Holding current                   | $V_{\rm D} = 12 \text{ V}; I_{\rm GT} = 0.1 \text{ A}$  | -       | 15          | 25  | 30       | mA       |
|                                   |                                   |   | D, E, F |             |     |          |          |
| V <sub>T</sub>                    | On-state voltage                  | I <sub>⊤</sub> = 20 A                                   | -       |             | 1.5 |          | V        |
| V <sub>T</sub><br>V <sub>GT</sub> | Gate trigger voltage              | $\dot{V}_{D} = 12 \text{ V}; I_{T} = 0.1 \text{ A}$     | -       |             | 1.5 |          | V        |
|                                   |                                   | $V_{\rm D} = 400 \text{ V}; I_{\rm T} = 0.1 \text{ A};$ | 0.25    |             | -   |          | V        |
| ,                                 | Off-state leakage current         | $T_{i} = 125 °C$  |         |             | 0.5 |          | mA       |
| I <sub>D</sub>                    | On-State leakage cullent          | $V_D = V_{DRM(max)}; T_j = 125 °C$                      | -       |             | 0.5 |          | IIIA     |

## **DYNAMIC CHARACTERISTICS**

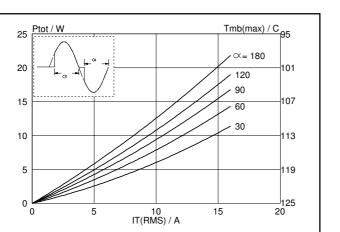
 $T_i = 25$  °C unless otherwise stated

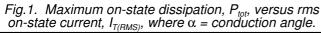
| SYMBOL                | PARAMETER   | CONDITIONS  | MIN. |     | MAX. | UNIT |      |
|-----------------------|---|---|------|-----|------|------|------|
|                       |   | BTA216-   | D    | E   | F    |      |      |
| dV <sub>D</sub> /dt   | Critical rate of rise of off-state voltage        | $V_{DM} = 67\% V_{DRM(max)};$<br>$T_j = 110 °C;$ exponential<br>waveform; gate open<br>circuit  | 30   | 60  | 70   | -    | V/µs |
| dl <sub>com</sub> /dt | Critical rate of change of<br>commutating current | $V_{DM} = 400 \text{ V}; \text{T}_{j} = 125 ^{\circ}\text{C};$<br>$I_{T(RMS)} = 16 \text{ A};$<br>$dV_{com}/dt = 10V/\mu\text{s}; \text{ gate}$<br>open circuit | 2.5  | 6.2 | 18   | -    | A/ms |
| dl <sub>com</sub> /dt | Critical rate of change of<br>commutating current | $V_{DM} = 400 \text{ V}; \text{ T}_{j} = 125 \text{ °C};$<br>$I_{T(RMS)} = 16 \text{ A};$<br>$dV_{com}/dt = 0.1 \text{ V}/\mu\text{s};$ gate<br>open circuit    | 12   | 20  | 50   | -    | A/ms |

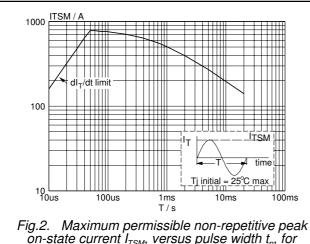
**<sup>2</sup>** Device does not trigger in the T2-, G+ quadrant.

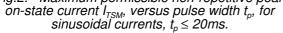
BTA216 series D, E and F

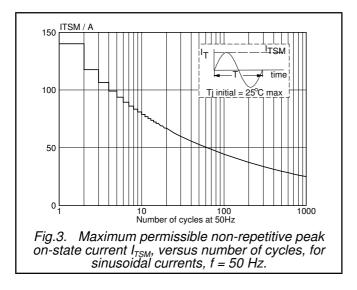
## Three quadrant triacs guaranteed commutation

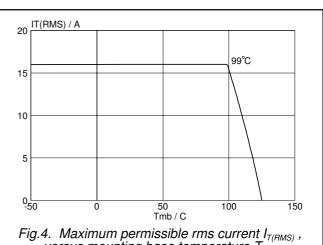


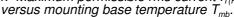


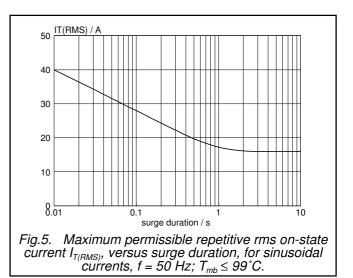


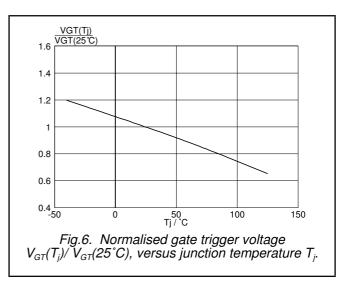












BTA216 series D, E and F

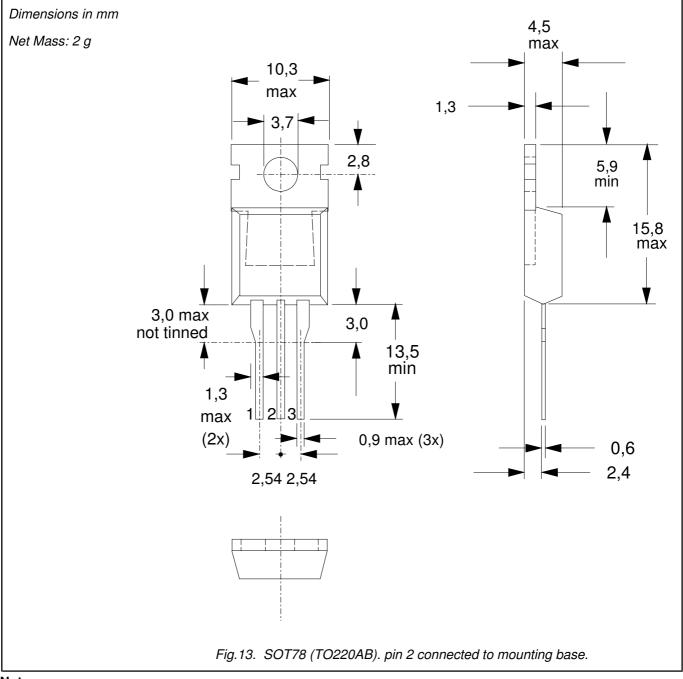
## Three quadrant triacs guaranteed commutation

#### IT / A IGT(Tj) IGT(25℃) 50 Tj = 125 C Tj = 25 C 3 — T2+ G+ — T2+ Gtyp ma - T2- G-40 2.5 Vo = 1.195 V Rs = 0.018 Ohms 2 30 1.5 20 1 10 0.5 0 L 0 0 1.5 VT / V 150 0.5 2 2.5 3 -50 0 тј/℃ 100 1 Fig.7. Normalised gate trigger current $I_{GT}(T_j)/I_{GT}(25^{\circ}C)$ , versus junction temperature $T_{j}$ . Fig.10. Typical and maximum on-state characteristic. 10 \_\_\_\_\_(K/W) IL(Tj) IL(25°C) 3 25 1 bidirectional 2 0.1 1.5 1 0.01 0.5 0.001 – 10us 0 -50 0.1ms 10ms 0.1s 1s 10s 50 Tj /℃ 100 1ms 0 150 tp/s Fig.11. Transient thermal impedance $Z_{th j-mb}$ , versus Fig.8. Normalised latching current $I_L(T_i)/I_L(25^{\circ}C)$ , versus junction temperature $T_{i}$ pulse width $t_{\rm p}$ . dlcom/dt (A/ms) IH(Tj) 100 3 IH(25°C F TYPE E TYPE D TYPE 2.5 2 10 1.5 1 0.5 1 0 -50 50 Tj /℃ 20 40 60 100 120 140 100 150 80 Tj/°C 0 Fig.9. Normalised holding current $I_H(T_i)/I_H(25^{\circ}C)$ , versus junction temperature $T_j$ . Fig.12. Minimum, critical rate of change of commutating current $dI_{com}/dt$ versus junction temperature, $dV_{com}/dt = 10V/\mu s$ .

# Three quadrant triacs guaranteed commutation

## BTA216 series D, E and F

## **MECHANICAL DATA**



Notes 1. Refer to mounting instructions for SOT78 (TO220) envelopes. 2. Epoxy meets UL94 V0 at 1/8".

## Legal information

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| DOCUMENT<br>STATUS <sup>(1)</sup> | PRODUCT<br>STATUS <sup>(2)</sup> | DEFINITION  |
|-----------------------------------|----------------------------------|---|
| Objective data sheet              | Development                      | This document contains data from the objective specification for product development. |
| Preliminary data sheet            | Qualification                    | This document contains data from the preliminary specification.                       |
| Product data sheet                | Production                       | This document contains the product specification.                                     |

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